

Protection Device

TVS (Transient Voltage Suppressor)

ESD307-U1-02N

Uni-directional, 10 V, 270 pF, 0603, RoHS and Halogen Free compliant

ESD307-U1-02N

Data Sheet

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Final

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Page or Item	Subjects (major changes since previous revision)
Revision 1.0, 2014-05-30	
All	Curves included

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Last Trademarks Update 2010-10-26

1 Product Overview

1.1 Features

- ESD / Transient / Surge protection according to:
 - IEC61000-4-2 (ESD): ± 30 kV (air / contact discharge)
 - IEC61000-4-4 (EFT): ± 4 kV / ± 80 A (5/50 ns)
 - IEC61000-4-5 (surge): ± 34 A (8/20 μ s)
- Uni-directional working voltage up to $V_{RWM} = 10$ V
- Low capacitance: $C_L = 270$ pF (typical)
- Low clamping voltage $V_{CL} = 24$ V (typical) at $I_{PP} = 34$ A
- Low reverse current. $I_R < 1$ nA (typical)
- Small and flat-profile SMD plastic package: 1.6 mm x 0.8 mm x 0.375 mm.
- Pb-free (RoHS compliant) and halogen free package



1.2 Application Examples

- Surge protection of USB V_{BUS} lines in mobile devices

1.3 Product Description

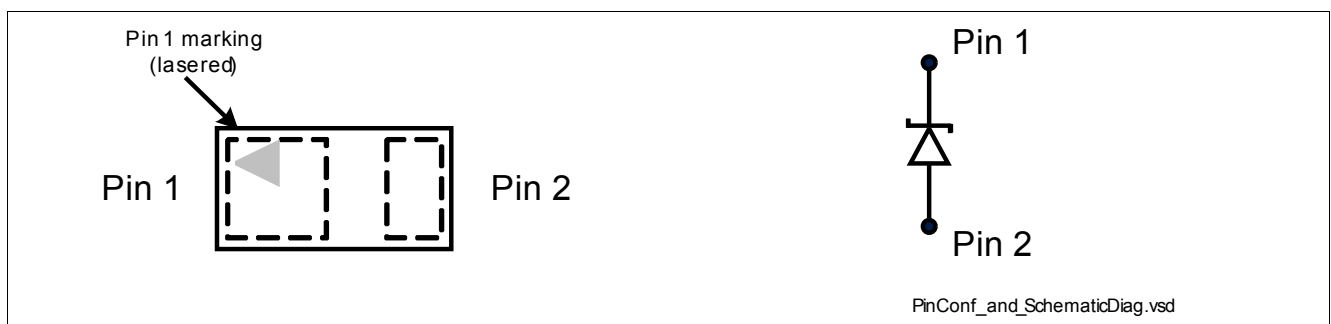


Figure 1-1 Pin Configuration and Schematic Diagram (in mm)

Table 1-1 Ordering Information

Type	Package	Configuration	Marking code
ESD307-U1-02N	TSNP-2-2	uni-directional	7

2 Characteristics

Table 2-1 Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values	Unit
ESD air / contact discharge ¹⁾	V_{ESD}	± 30	kV
Peak pulse power ²⁾	P_{PK}	800	W
Peak pulse current ²⁾	I_{PP}	34	A
Operating temperature range	T_{OP}	-40 to 125	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to 150	$^\circ\text{C}$

1) V_{ESD} according to IEC61000-4-2

2) Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

3 Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

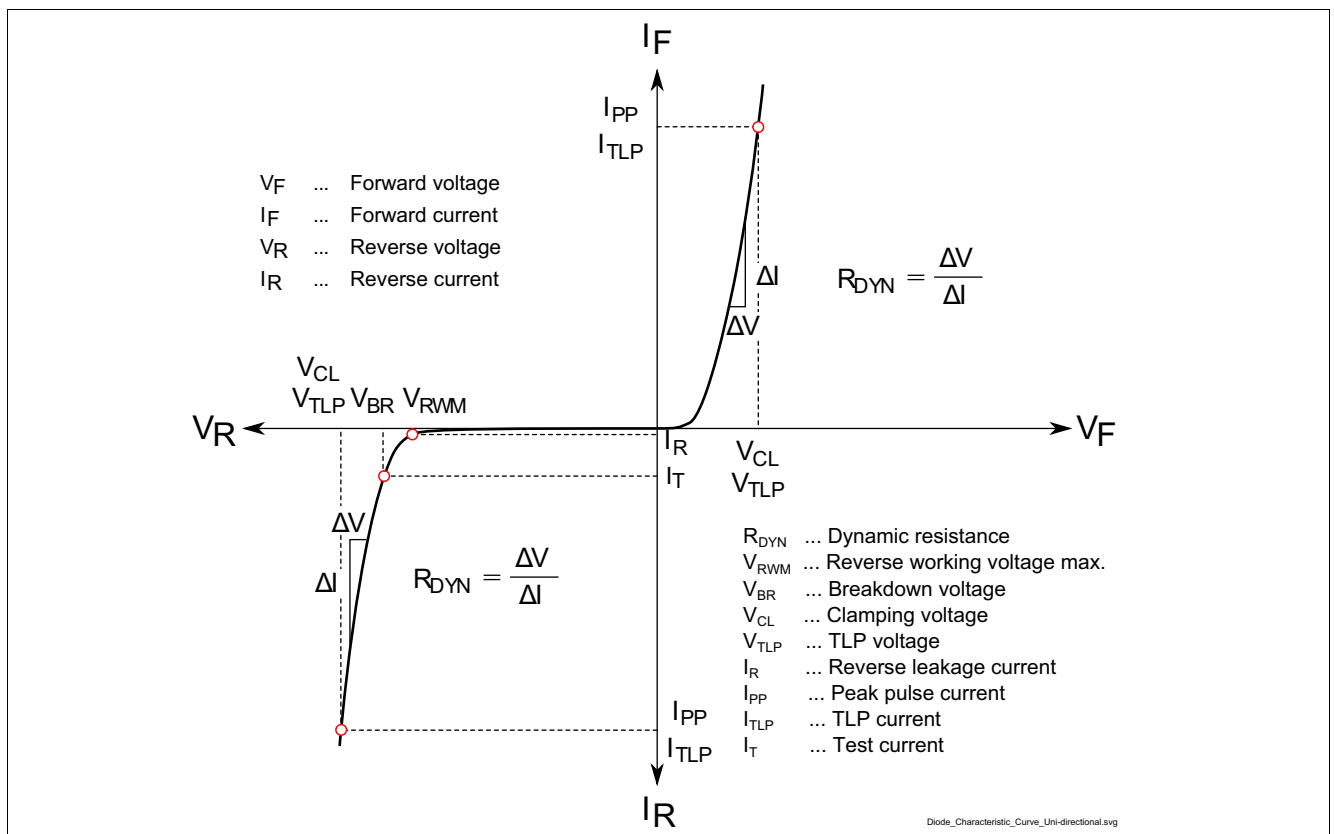


Figure 3-1 Definitions of electrical characteristics

Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified
Table 3-1 DC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	–	–	10	V	
Breakdown voltage	V_{BR}	11.1	12.1	–	V	$I_T = 1\text{ mA}$
Reverse current	I_R	–	<1	100	nA	$V_R = 10\text{V}$

Table 3-2 AC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	–	270	350	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$

Table 3-3 ESD and Surge Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage ¹⁾	V_{CL}	–	17	20.5	V	$I_{TLP} = 16\text{ A}, t_p = 100\text{ ns}$
		–	18	22		$I_{TLP} = 30\text{ A}, t_p = 100\text{ ns}$
Clamping voltage ²⁾		–	16	19.5		$I_{PP} = 1\text{ A}, t_p = 8/20\text{ }\mu\text{s}$
		–	24	29		$I_{PP} = 34\text{ A}, t_p = 8/20\text{ }\mu\text{s}$
Dynamic resistance ¹⁾	R_{DYN}	–	0.05	–	Ω	$t_p = 100\text{ ns}$

1) Please refer to Application Note AN210[1]. TLP parameter: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 600\text{ps}$.

2) Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5

4 Typical Characteristics Diagrams

Typical characteristics diagrams at $T_A = 25^\circ\text{C}$, unless otherwise specified

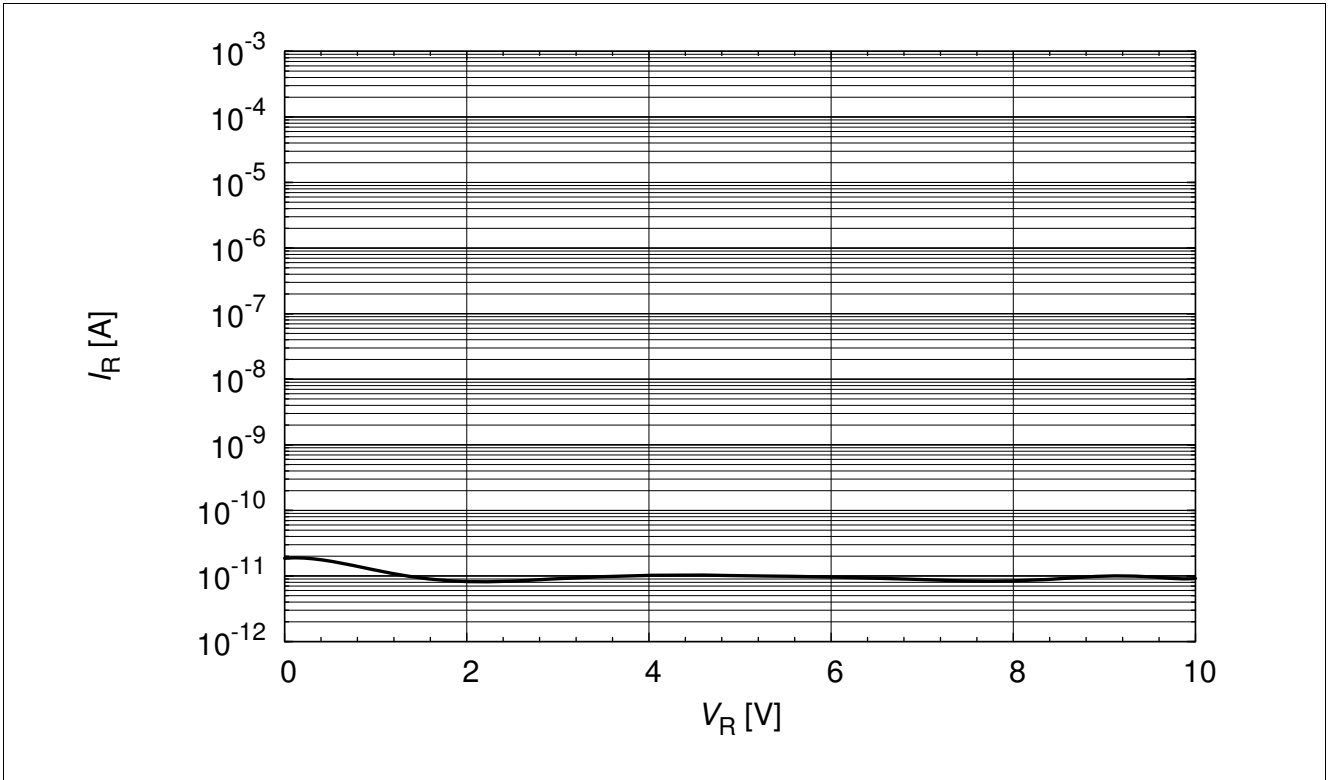


Figure 4-1 Reverse leakage current: $I_R = f(V_R)$

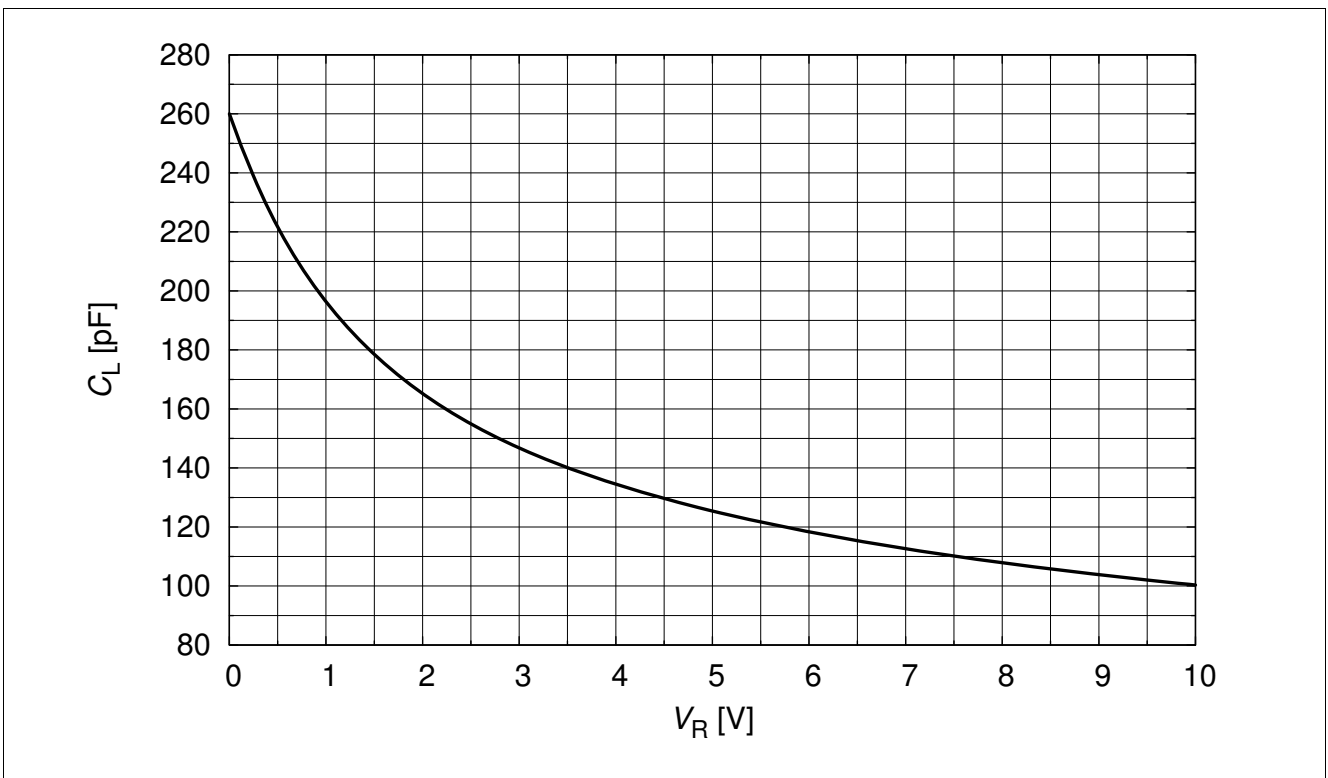


Figure 4-2 Line capacitance: $C_L = f(V_R)$

Typical Characteristics Diagrams

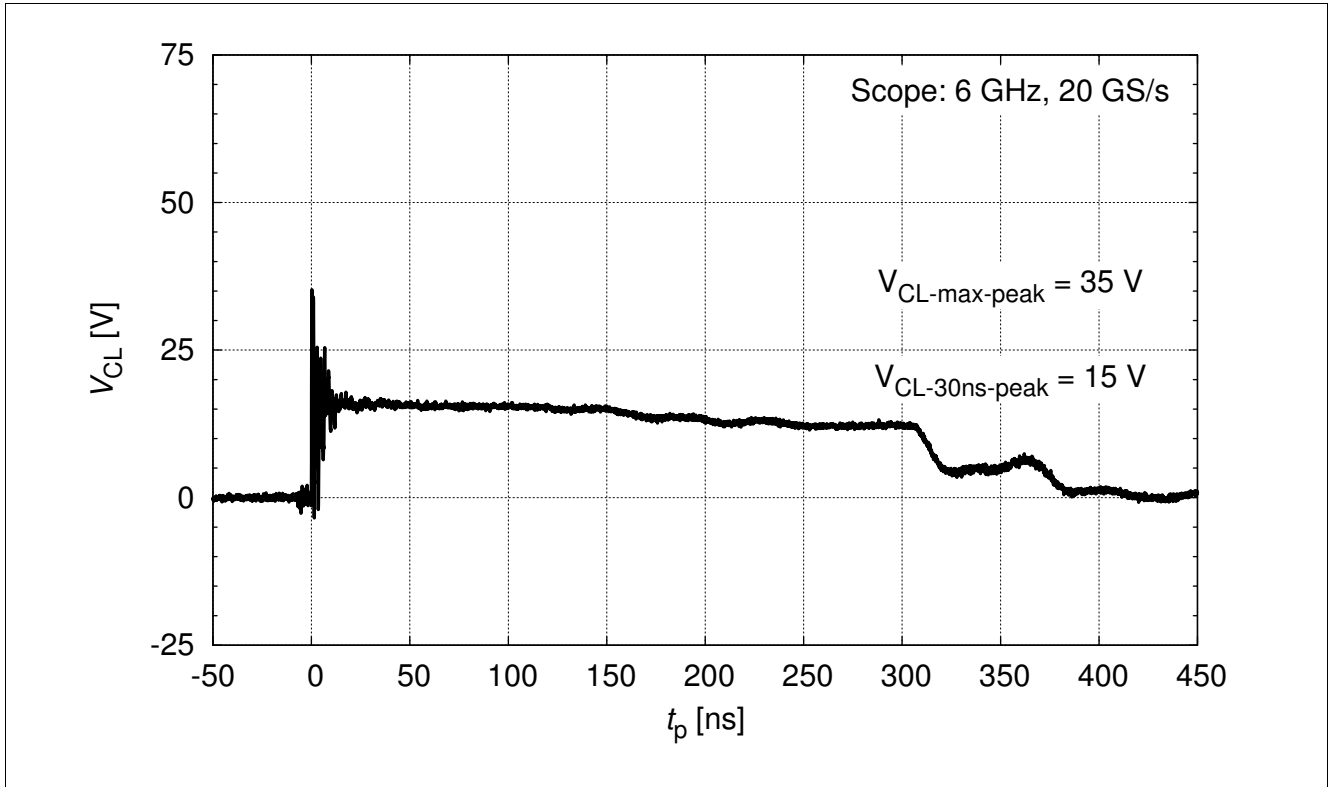


Figure 4-3 Clamping voltage (ESD): $V_{CL} = f(t)$, 8 kV positive pulse from pin 1 to pin 2

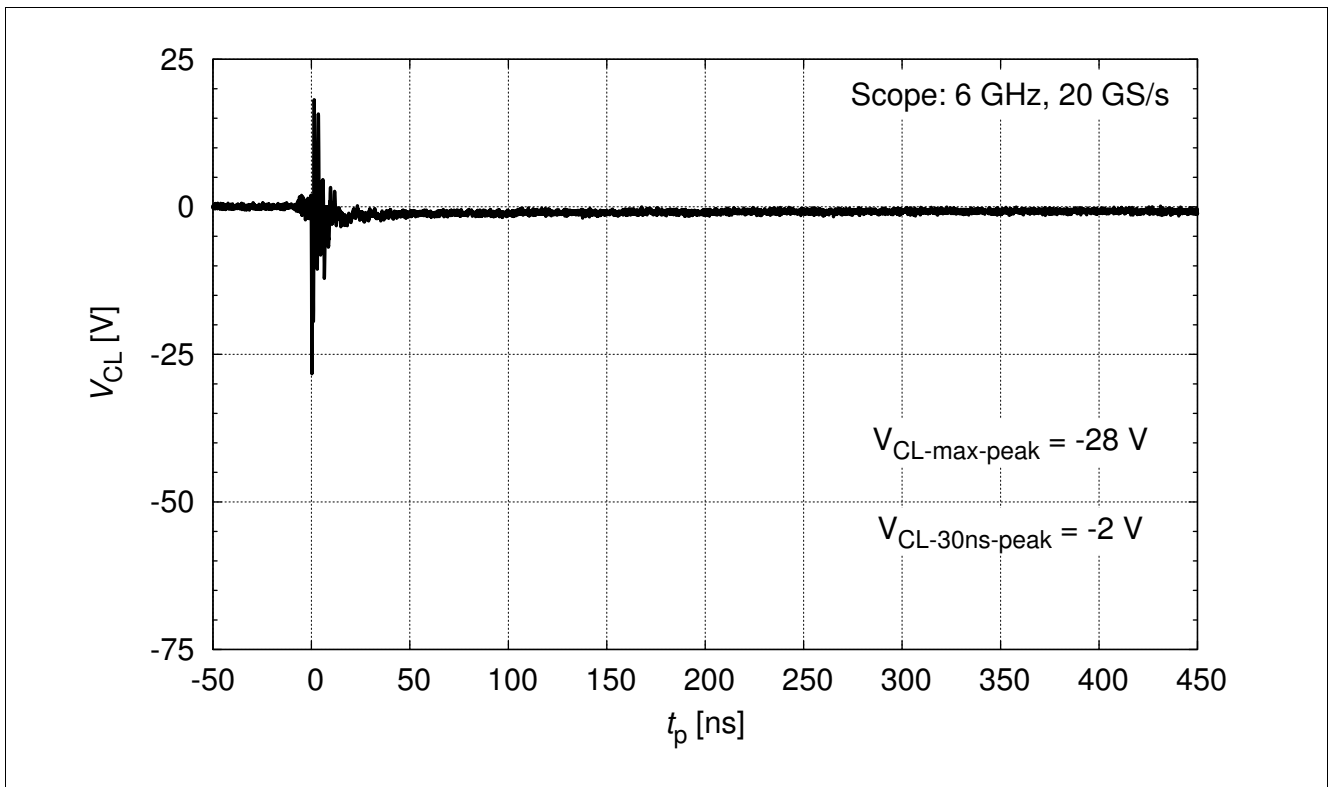


Figure 4-4 Clamping voltage (ESD) $V_{CL} = f(t)$, 8 kV negative pulse from pin 1 to pin 2

Typical Characteristics Diagrams

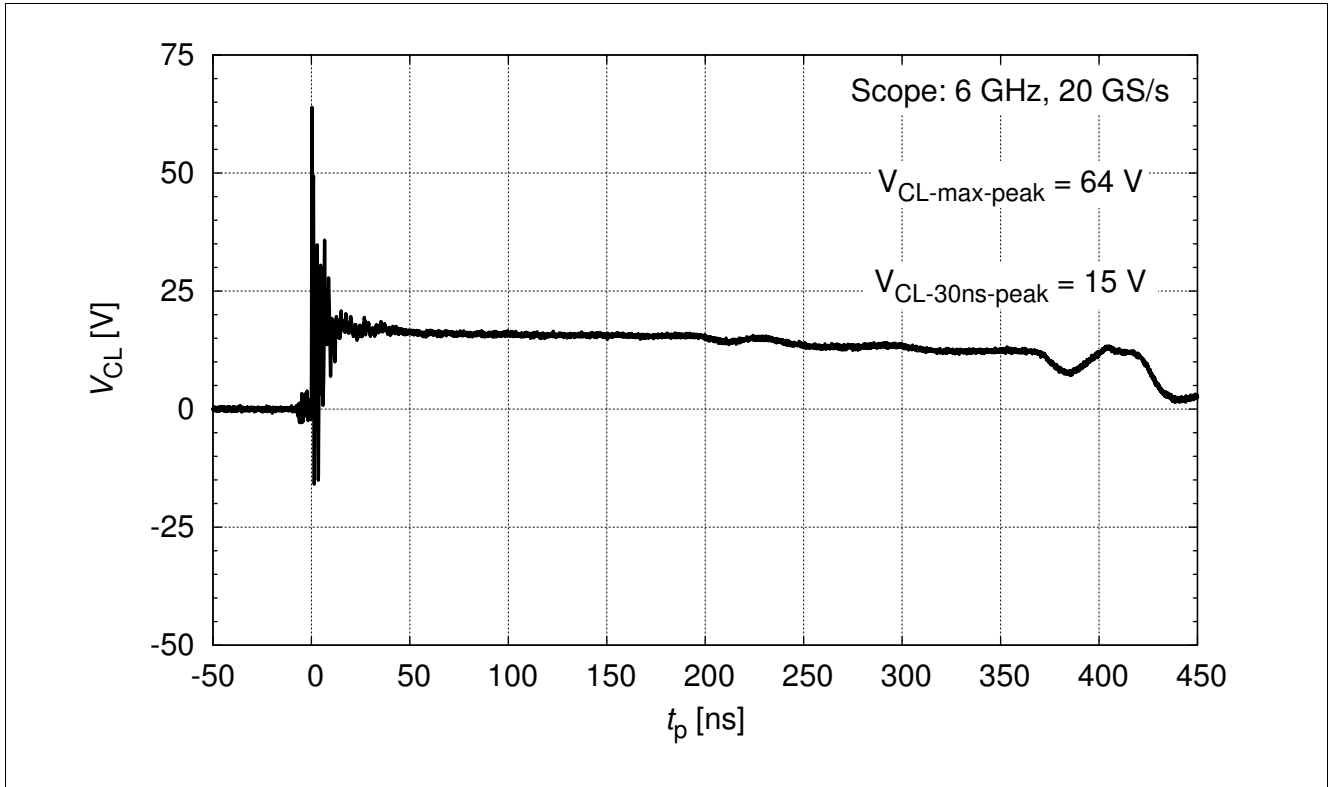


Figure 4-5 Clamping voltage (ESD) $V_{CL} = f(t)$, 15 kV positive pulse from pin 1 to pin 2

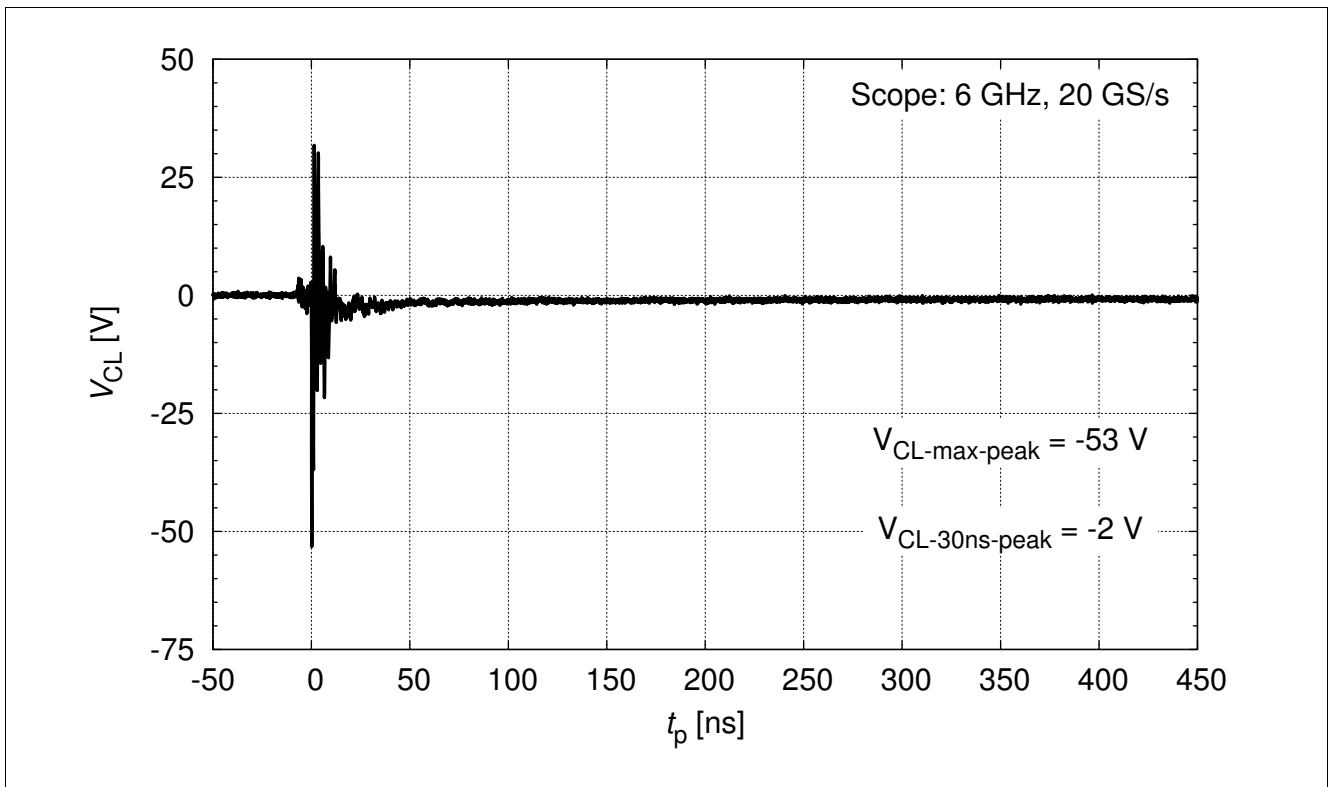


Figure 4-6 Clamping voltage (ESD) $V_{CL} = f(t)$, 15 kV negative pulse from pin 1 to pin 2

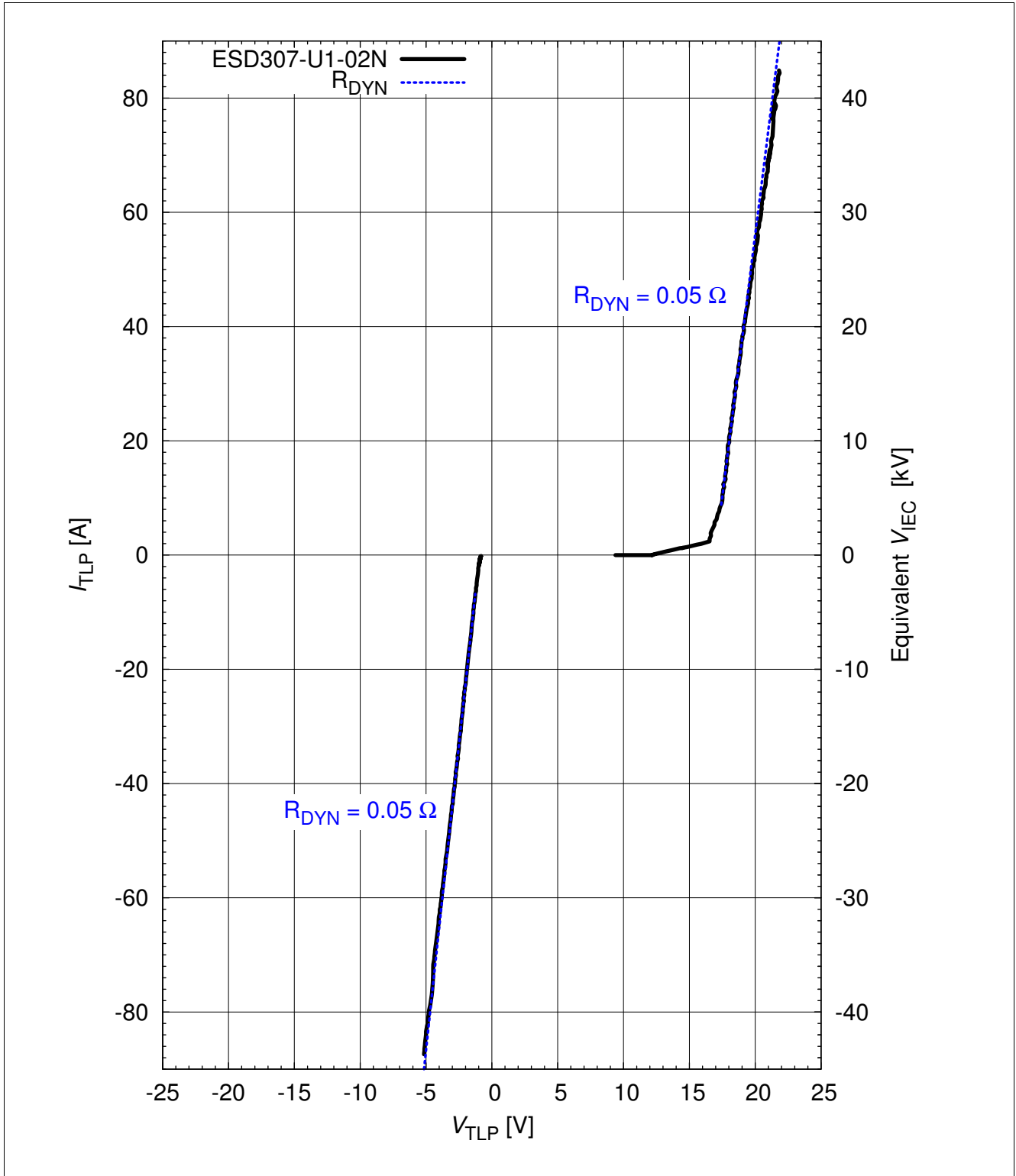


Figure 4-7 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$ [1], pin 1 to pin 2

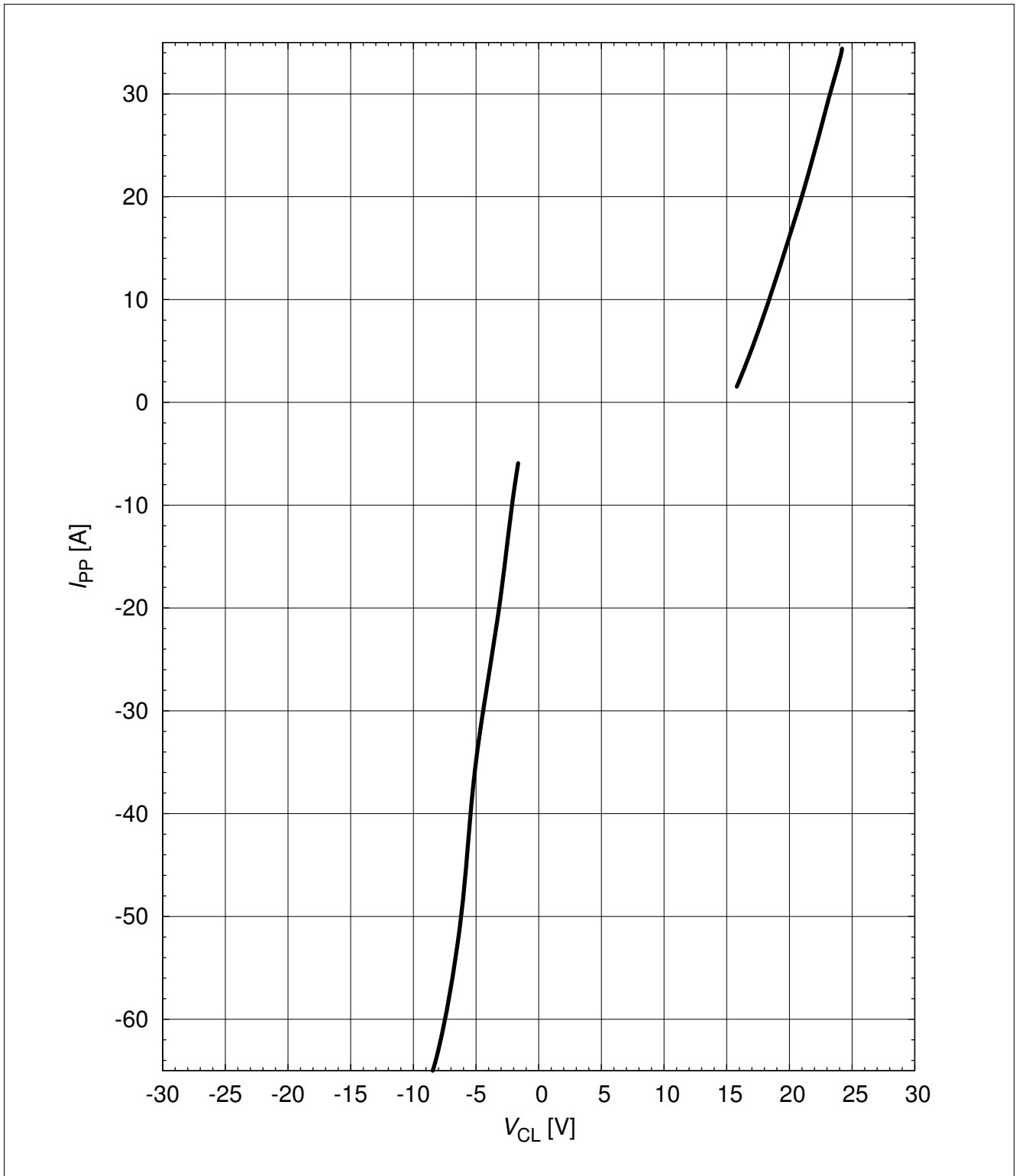


Figure 4-8 Pulse current (Surge): $I_{PP} = f(V_{CL})$ [1], pin 1 to pin 2

5 Package Information

5.1 TSNP-2-2

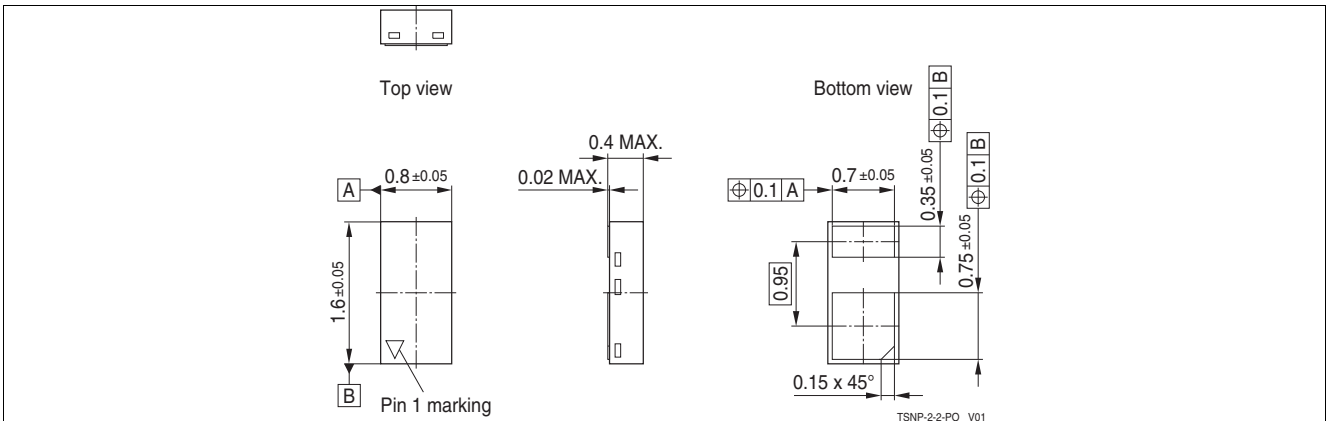


Figure 5-1 TSNP-2-2: Package overview

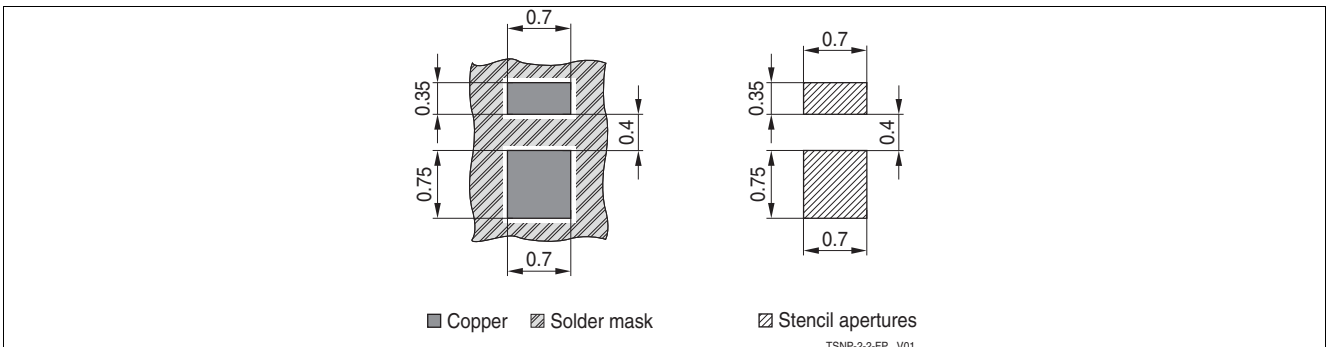


Figure 5-2 TSNP-2-2: Footprint

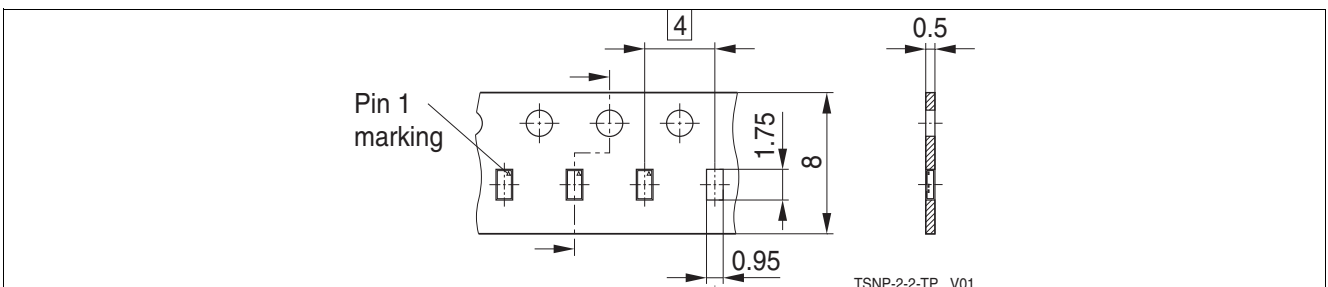


Figure 5-3 TSNP-2-2: Packing

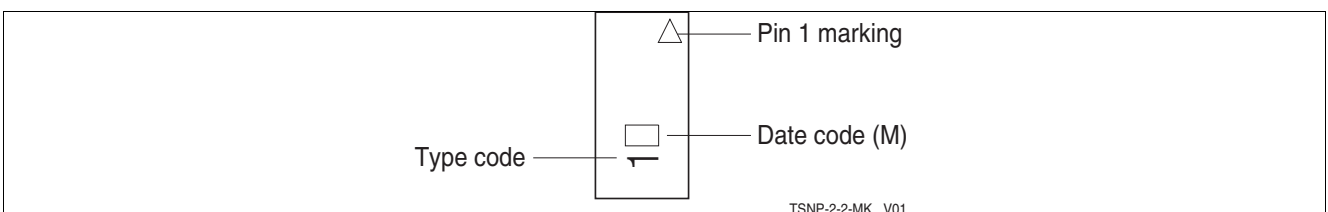


Figure 5-4 TSNP-2-2: Marking (example)

References

- [1] Infineon AG - **Application Note AN210: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology**
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Packages

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